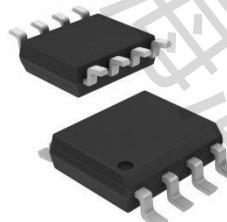
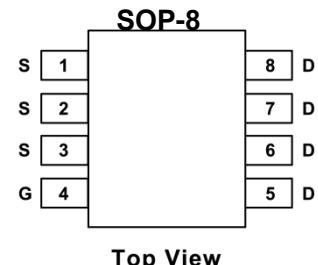


## SQ9407EY-T1-GE3-HX

## P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY	
$V_{DS}$	-60V
$R_{DS(ON)}$ (at $V_{GS}=-10V$ )	< 100mΩ
$R_{DS(ON)}$ (at $V_{GS} = -4.5V$ )	< 130mΩ
$I_D$ (at $V_{GS}=-10V$ )	-4A



## FEATURES

- TrenchFET® Power MOSFET
- 100 %  $R_g$  Tested

Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		$V_{DS}$	-60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ C$	$I_D$	-4	A
	$T_A=70^\circ C$		-3.1	
Pulsed Drain Current <sup>B</sup>		$I_{DM}$	-20	
Power Dissipation <sup>A</sup>	$T_A=25^\circ C$	$P_D$	3.1	W
	$T_A=70^\circ C$		2	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 to 150	°C

## Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$t \leq 10s$	$R_{\theta JA}$	24	40	°C/W
Maximum Junction-to-Ambient <sup>A</sup>	Steady-State		54	75	°C/W
Maximum Junction-to-Lead <sup>C</sup>	Steady-State	$R_{\theta JL}$	21	30	°C/W

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-60			V
IDSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-48V, V <sub>GS</sub> =0V			-1	μA
		T <sub>J</sub> =55°C			-5	
IGSS	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DSS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-2.1	-3	V
RDS(ON)	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A		80	100	mΩ
		T <sub>J</sub> =125°C		130		
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A		102	130	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-4A		10		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.77	-1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				-4	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V,		930	1120	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-30V,		85		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1MHz		35		pF
R <sub>g</sub>	Gate resistance	f=1MHz		7.2	9	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-30V, I <sub>D</sub> =-4A		16	20	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			8	10	nC
Q <sub>gs</sub>	Gate Source Charge			2.5		nC
Q <sub>gd</sub>	Gate Drain Charge			3.2		nC
t <sub>D(on)</sub>	Turn-On Delay Time	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-30V, R <sub>L</sub> =7.5Ω,		8		ns
t <sub>r</sub>	Turn-On Rise Time			3.8		ns
t <sub>D(off)</sub>	Turn-Off Delay Time			31.5		ns
t <sub>f</sub>	Turn-Off Fall Time			7.5		ns
trr	Body Diode Reverse Recovery Time	I <sub>F</sub> =-4A, dI/dt=100A/μs		27	35	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =-4A, dI/dt=100A/μs		32		nC

**Notes:**

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t<sub>θJA</sub> ≤ 10s thermal resistance rating.

B. Repetitive rating, pulse width limited by junction temperature.

C. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

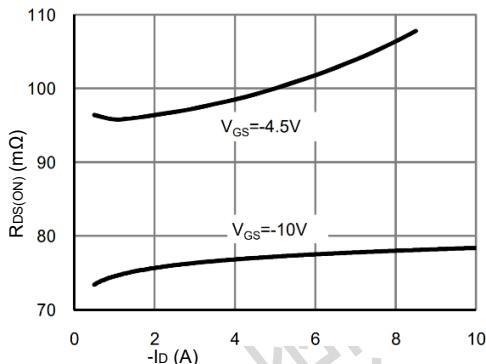


Fig 1. On-Resistance vs. Drain Current and Gate Voltage

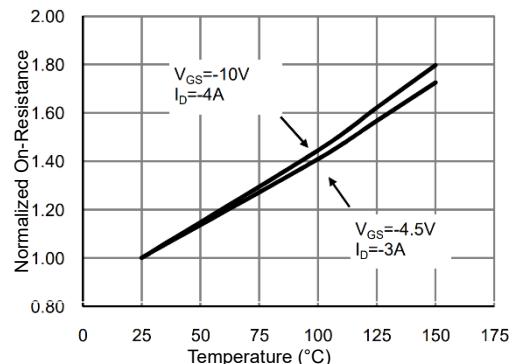


Fig 2. On-Resistance vs. Junction Temperature

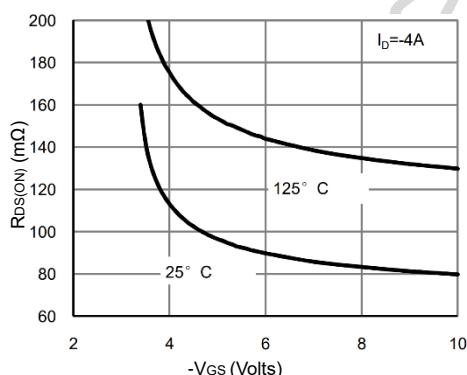


Fig 3. On-Resistance vs. Gate-Source Voltage

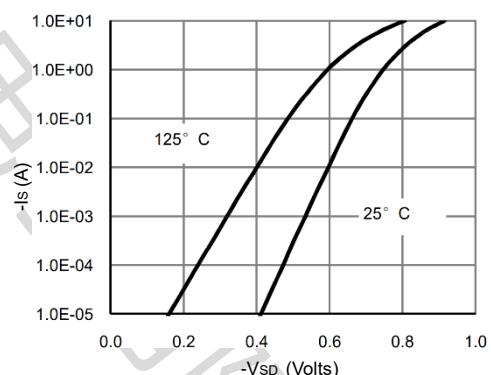


Fig 4. Body-Diode Characteristics

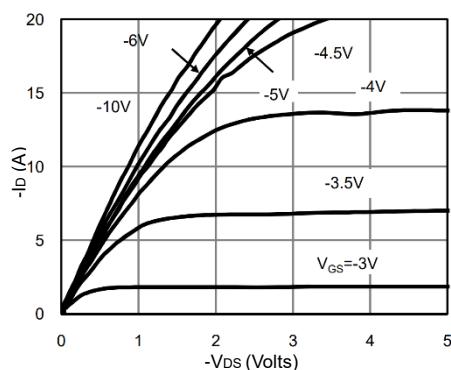


Fig 5. On-Region Characteristics

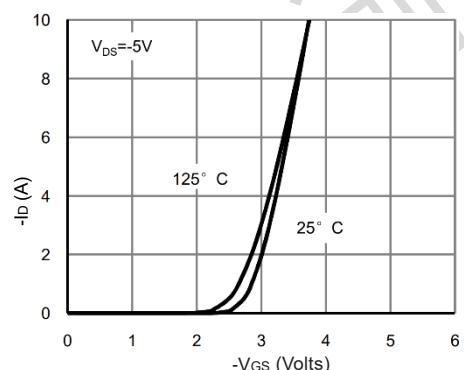


Fig 6. Transfer Characteristics

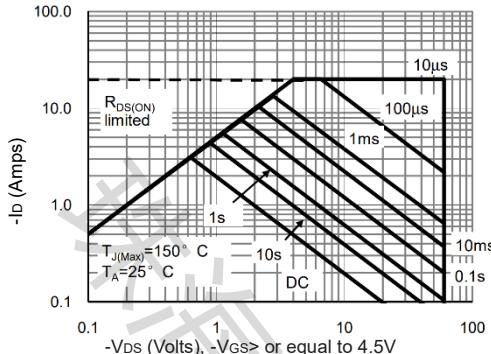


Fig 7. Maximum Forward Biased Safe Operating Area (Note E)

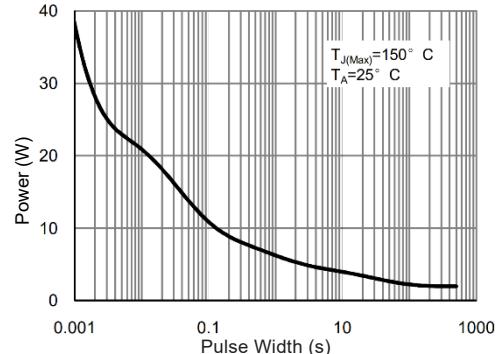


Fig 8. Single Pulse Power Rating Junction-to-Ambient (Note E)

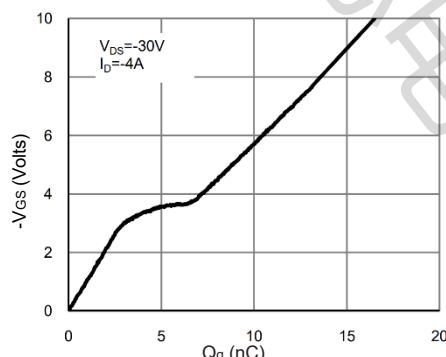


Fig 9. Gate-Charge Characteristics

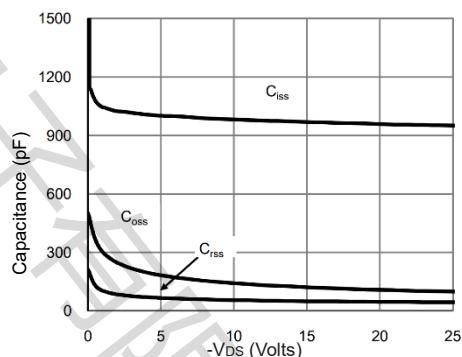


Fig 10. Capacitance Characteristics

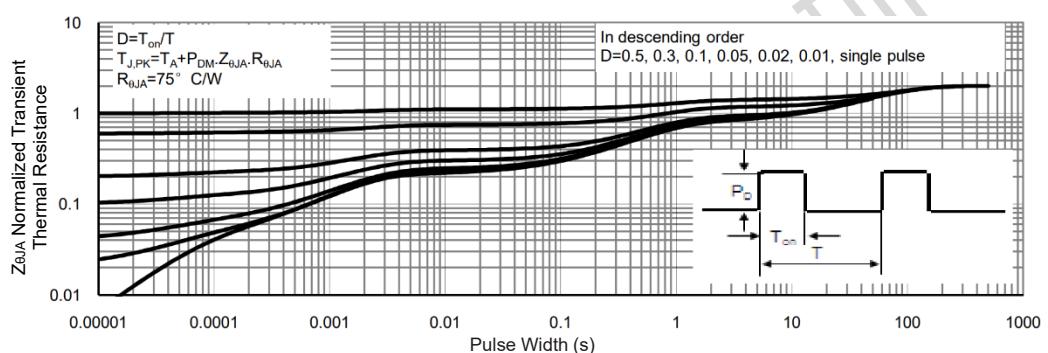
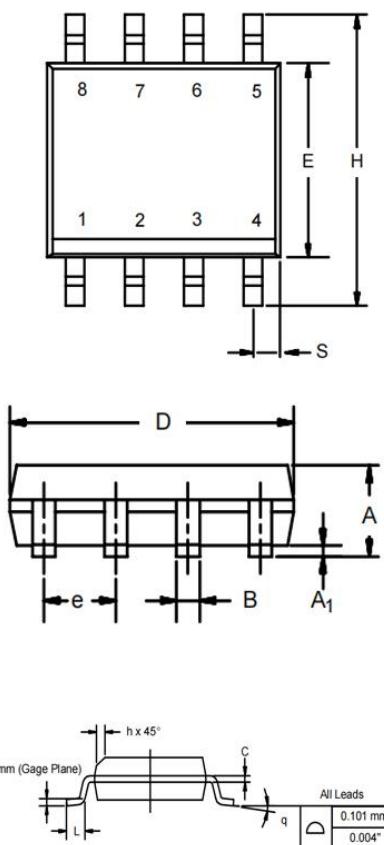


Fig 11. Normalized Maximum Transient Thermal Impedance

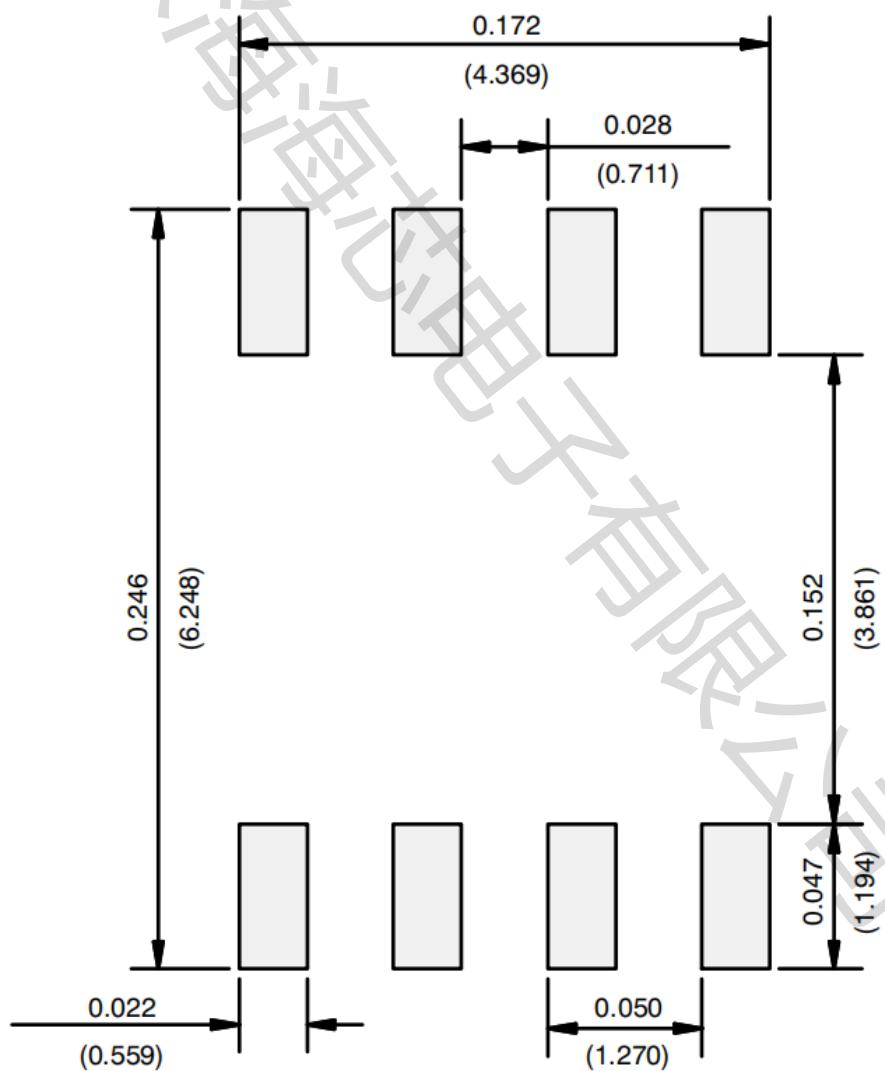
**SOP-8 Package Outline**

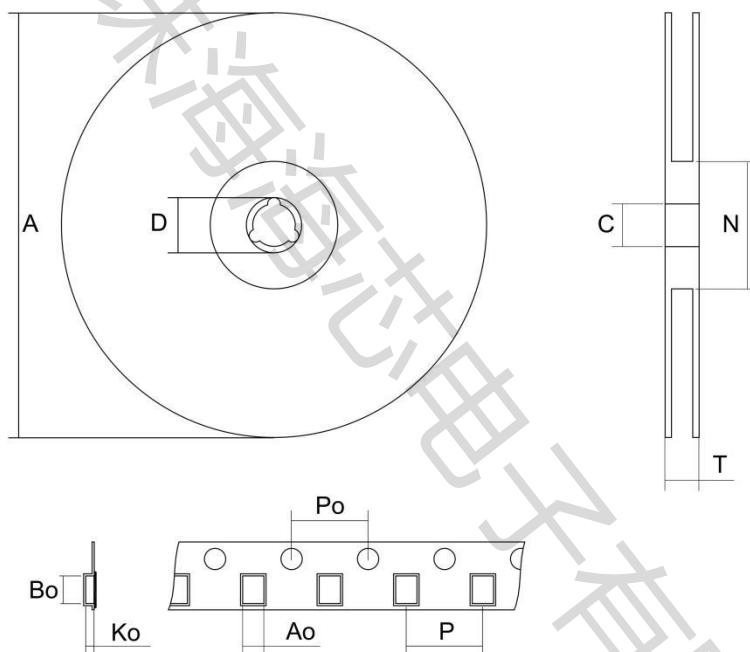
Dimensions are shown in millimeters (inches)



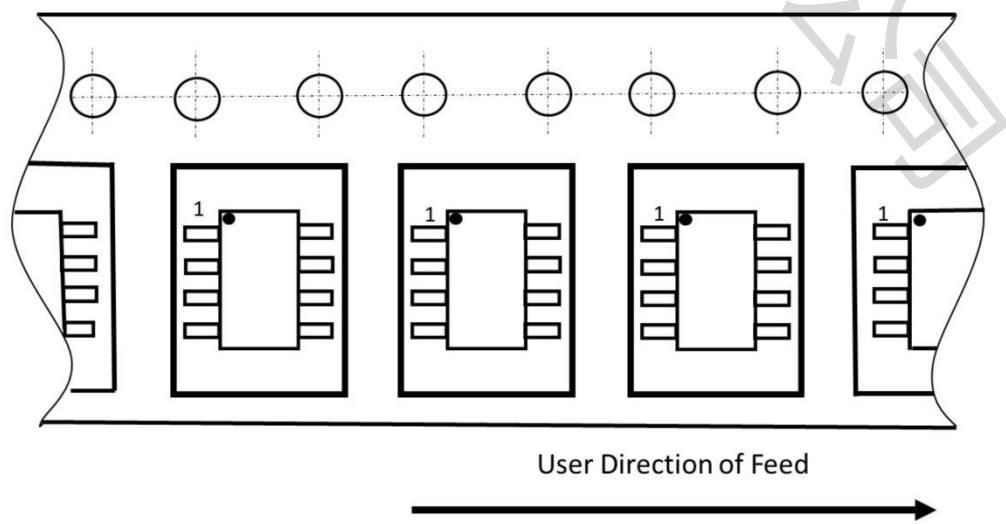
DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026

## RECOMMENDED MINIMUM PADS FOR SOP-8



**SOP-8 packing information****SOP-8 tape and reel****Tape orientation**

TYPICAL



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